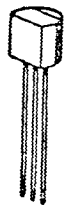
MICRO ELECTRONICS

NPN SILICON TRANSISTOR

DESCRIPTION

2N3414 is NPN silicon transistor designed for general purpose AF medium power applications.

TO-92



ECB

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCEO	25V
Collector-Emitter Voltage	VCBO	25V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	500mA
Operating & Storage Junction Temperature	Tj,Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	25		V	IC=100μA IE=0
Collector-Emitter Breakdown Voltage	BVCEO	25		V	IC=10mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA IC=0
Collector Cutoff Current	ICBO		100	nA	VCB=50V IE=0
Emitter Cutoff Current	IEBO		100	nA	VEB=5V IC=0
D.C. Current Gain	HFE	75	225		IC=2mA VCE=4.5V
Collector-Emitter Saturation Voltage	VCE(sat)		0.3	V	IC=50mA IB=3mA
Base-Emitter Saturation Voltage	VBE(sat)		0.85	V	IC=50mA IB=3mA
Small Signal Current Gain	hfe	300	TYP		IC=1mA VCE=10V f=1KHz

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